



General Description

The WSF55P06 is the highest performance trench P-ch MOSFETs with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The WSF55P06 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

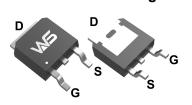
Product Summery

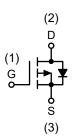
BVDSS	RDSON	ID
-60V	23mΩ	-50A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- CCFL Back-light Inverter

TO-252-2L Pin Configuration





Absolute Maximum Ratings (Tc=25 ℃, unless otherwise noted)

Symbol	Parameter	Limit	Unit
VDS	Drain-Source Voltage	-60	V
Vgs	Gate-Source Voltage	±20	V
lσ	Drain Current-Continuous	-50	А
I _D (T _C =100 [°] C)	Drain Current-Continuous(Tc=100℃)	-24.8	А
Ідм	Pulsed Drain Current	-220	А
P□	Maximum Power Dissipation	110	W
	Derating factor	0.73	W/°C
Eas	Single pulse avalanche energy (Note 5)	273	mJ
TJ,Tstg	Operating Junction and Storage Temperature Range -55 To 175		$^{\circ}$
Reлc	Thermal Resistance, Junction-to-Case(Note 2)	1.36	°C/W



Electrical Characteristics (Tc=25 °C,unless otherwise noted)

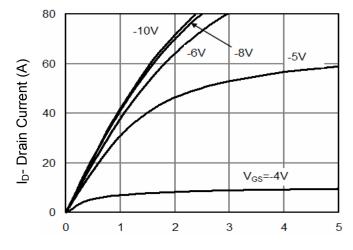
Symbol	Parameter	Condition	Min	Тур	Max	Unit
Off Characte	eristics					
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =-250µA	-60			V
Ipss	Zero Gate Voltage Drain Current	V _{DS} =-60V,V _{GS} =0V			-1	μΑ
lgss	Gate-Body Leakage Current	V _{GS} =±20V,V _{DS} =0V			±100	nA
On Characte	eristics (Note 3)					
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} ,I _D =-250μA	-1	-1.8	-3.0	V
RDS(ON)	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-20A		23	28	mΩ
g FS	Forward Transconductance	V _{DS} =-5V,I _D =-20A		25		S
Dynamic Ch	aracteristics (Note4)			1	<u>I</u>	<u>I</u>
Ciss	Input Capacitance			3017		PF
Coss	Output Capacitance	V _{DS} =-30V,V _{GS} =0V, f=1.0MHz		180		PF
Crss	Reverse Transfer Capacitance			126		PF
Switching C	haracteristics (Note 4)				•	•
td(on)	Turn-on Delay Time			12		nS
tr	Turn-on Rise Time	V _{DD} =-30V, R _L =1.5Ω,		15		nS
td(off)	Turn-Off Delay Time	V _{GS} =-10V,R _G =3Ω		15		nS
tf	Turn-Off Fall Time	1		38		nS
Qg	Total Gate Charge			49.8		nC
Qgs	Gate-Source Charge	V _{DS} =-30,I _D =-20A, V _{GS} =-		10.6		nC
Qgd	Gate-Drain Charge			13.6		nC
Drain-Source	e Diode Characteristics			•	•	•
Vsp	Diode Forward Voltage (Note 3)	V _{GS} =0V,I _S =-20A			-1.2	V
ls	Diode Forward Current (Note 2)				-50	Α
trr	Reverse Recovery Time	TJ = 25°C, IF =- 20A		47		nS
Qrr	Reverse Recovery Charge	$di/dt = -100A/\mu s_{(Note3)}$		53		nC

Notes:

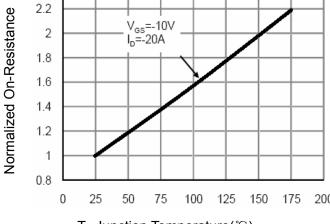
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- **5.** Eas condition: Tj=25 $^{\circ}$ C,VDD=-20V,VG=-10V,L=0.5mH,Rg=25 Ω



Typical Electrical and Thermal Characteristics (Curves)



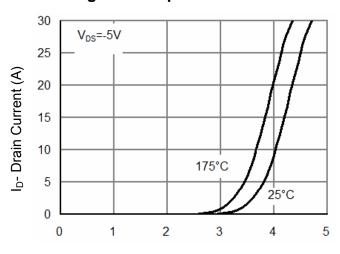
Vds Drain-Source Voltage (V)



2.4

T_J-Junction Temperature(°C)





Vgs Gate-Source Voltage (V)

Figure 4 Rdson-Junction Temperature

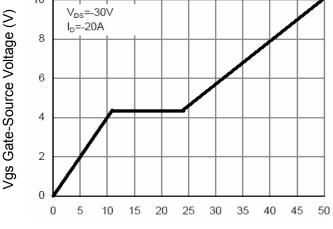


Figure 2 Transfer Characteristics

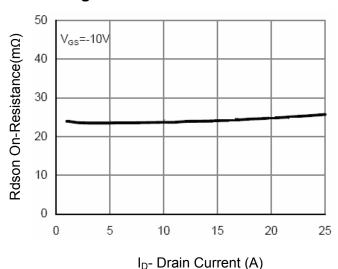


Figure 3 Rdson- Drain Current

Qg Gate Charge (nC)
Figure 5 Gate Charge

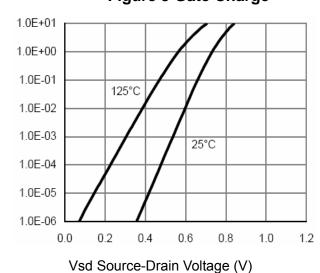


Figure 6 Source- Drain Diode Forward

Is- Reverse Drain Current (A)



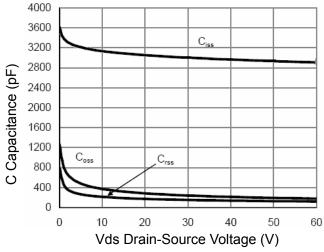
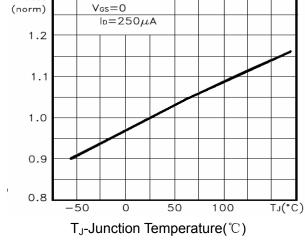


Figure 7 Capacitance vs Vds



BV_{DSS}

Figure 9 BV_{DSS} vs Junction Temperature

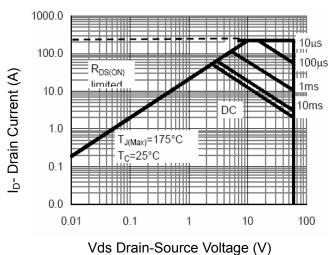


Figure 8 Safe Operation Area

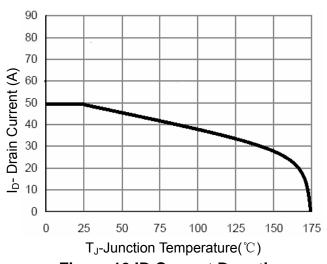


Figure 10 ID Current De-rating

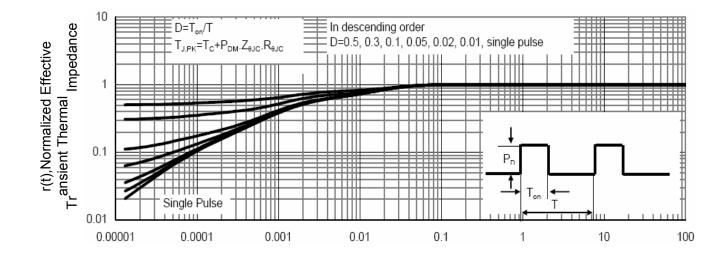
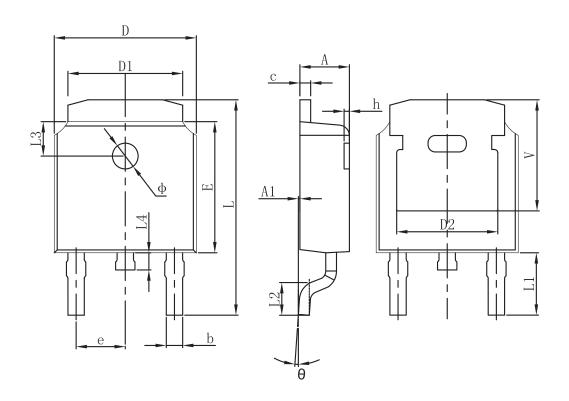


Figure 11 Normalized Maximum Transient Thermal Impedance

Square Wave Pluse Duration(sec)



Packaging information



Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.635	0.770	0.025	0.030	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.830 REF.		0.190 REF.		
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.712	10.312	0.382	0.406	
L1	2.900 REF.		0.114 REF.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 REF.		0.063 REF.		
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.250	REF.	0.207 REF.		



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